

Complementary 20-V (D-S) Low-Threshold MOSFET

PRODUCT SUMMARY

	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.280 at $V_{GS} = 4.5$ V	1.28
		0.360 at $V_{GS} = 2.5$ V	1.13
		0.450 at $V_{GS} = 1.8$ V	1.0
P-Channel	- 20	0.490 at $V_{GS} = - 4.5$ V	- 1.0
		0.750 at $V_{GS} = - 2.5$ V	- 0.81
		1.10 at $V_{GS} = - 1.8$ V	- 0.67

FEATURES

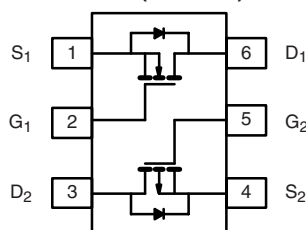
- TrenchFET® Power MOSFETS: 1.8 V Rated
- ESD Protected: 2000 V
- Thermally Enhanced SC-70 Package


RoHS*
COMPLIANT

APPLICATIONS

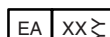
- Load Switching
- PA Switch
- Level Switch

SOT-363
SC-70 (6-LEADS)



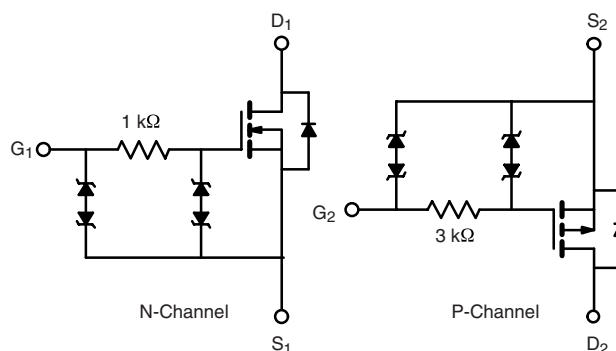
Top View

Marking Code



Lot Traceability
and Date Code

Part # Code



Ordering Information: Si1563EDH-T1
Si1563EDH-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	N-Channel		P-Channel		Unit
		5 s	Steady State	5 s	Steady State	
Drain-Source Voltage	V_{DS}	20		- 20		V
Gate-Source Voltage	V_{GS}	± 12		± 12		V
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	1.28	1.13	- 1.0	- 0.88	A
		0.92	0.81	- 0.72	- 0.63	
Pulsed Drain Current	I_{DM}	4.0		- 3.0		A
Continuous Source Current (Diode Conduction) ^a	I_S	0.61	0.48	- 0.61	- 0.48	A
Maximum Power Dissipation ^a	P_D	0.74	0.57	0.30	0.57	W
		0.38	0.30	0.16	0.3	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150				$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	130	170	$^\circ\text{C/W}$
	Steady State		170	220	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	80	100	$^\circ\text{C/W}$

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

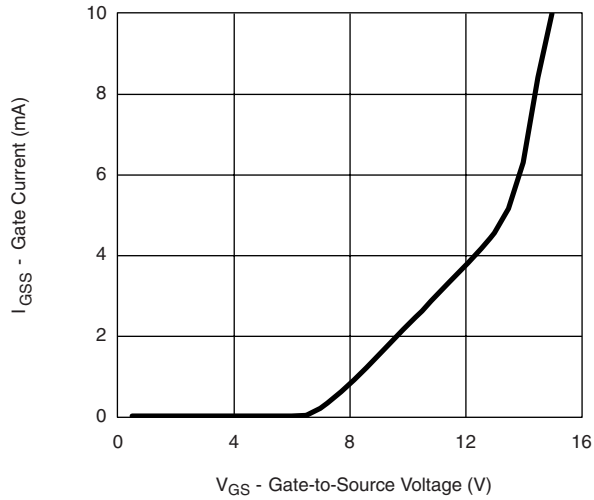
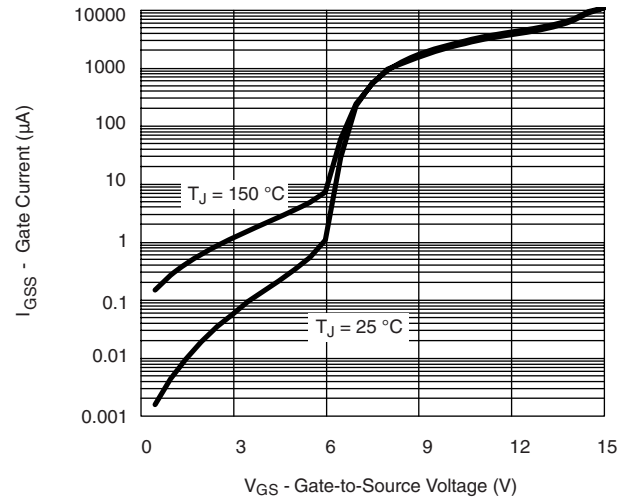
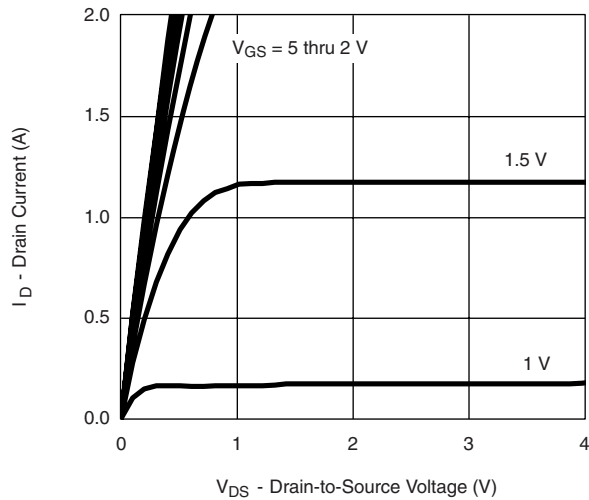
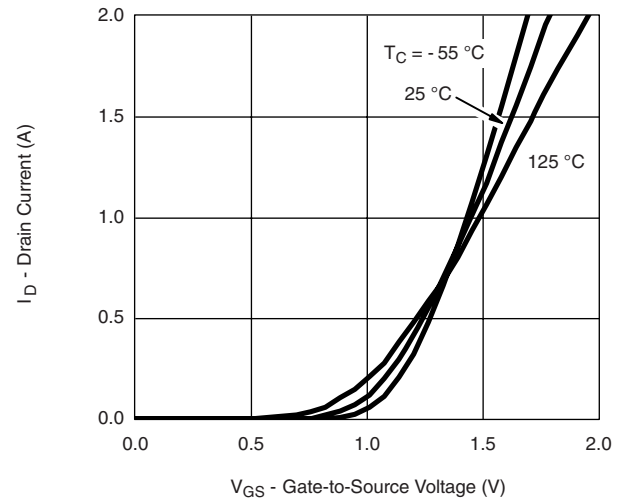
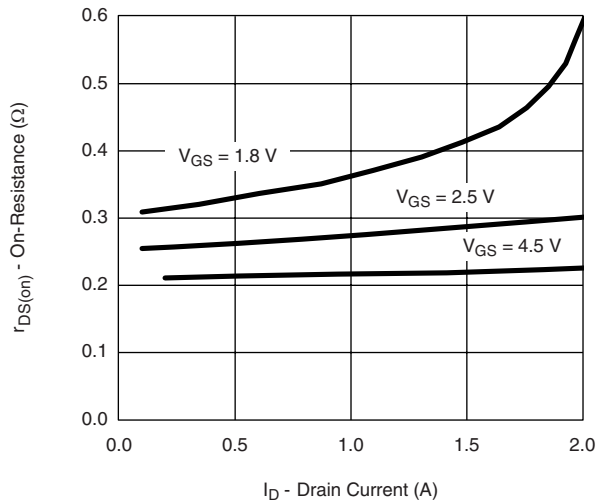
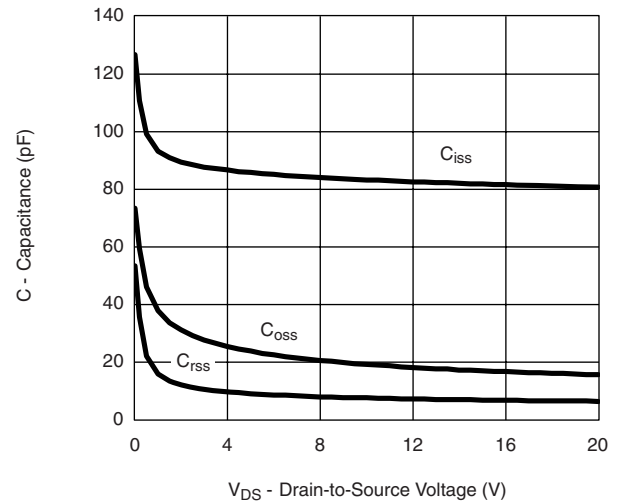
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 100 μA	N-Ch	0.45			V
		V _{DS} = V _{GS} , I _D = - 100 μA	P-Ch	- 0.45			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V	N-Ch			± 1	μA
			P-Ch			± 1	
		V _{DS} = 0 V, V _{GS} = ± 12 V	N-Ch			± 10	mA
			P-Ch			± 10	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 16 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 85 °C	N-Ch			5	
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C	P-Ch			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	2			A
		V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	P-Ch	- 2			
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 1.13 A	N-Ch		0.220	0.280	Ω
		V _{GS} = - 4.5 V, I _D = - 0.88 A	P-Ch		0.400	0.490	
		V _{GS} = 2.5 V, I _D = 0.99 A	N-Ch		0.281	0.360	
		V _{GS} = - 2.5 V, I _D = - 0.71 A	P-Ch		0.610	0.750	
		V _{GS} = 1.8 V, I _D = 0.20 A	N-Ch		0.344	0.450	
		V _{GS} = - 1.8 V, I _D = - 0.20 A	P-Ch		0.850	1.10	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 1.13 A	N-Ch		2.6		S
		V _{DS} = - 10 V, I _D = - 0.88 A	P-Ch		1.5		
Diode Forward Voltage ^a	V _{SD}	I _S = 0.48 V, V _{GS} = 0 V	N-Ch		0.8	1.2	V
		I _S = - 0.48 V, V _{GS} = 0 V	P-Ch		- 0.8	- 1.2	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 1.13 A	N-Ch		0.65	1.0	nC
			P-Ch		1.2	1.8	
Gate-Source Charge	Q _{gs}	P-Channel V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 0.88 A	N-Ch		0.2		
			P-Ch		0.3		
Gate-Drain Charge	Q _{gd}		N-Ch		0.23		
			P-Ch		0.3		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 10 V, R _L = 20 Ω I _D ≅ 0.5 A, V _{GEN} = 4.5 V, R _g = 6 Ω	N-Ch		45	70	ns
			P-Ch		150	230	
Rise Time	t _r		N-Ch		85	130	
			P-Ch		480	720	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 10 V, R _L = 20 Ω I _D ≅ - 0.5 A, V _{GEN} = - 4.5 V, R _g = 6 Ω	N-Ch		350	530	
			P-Ch		840	1200	
Fall Time	t _f		N-Ch		210	320	
			P-Ch		850	1200	

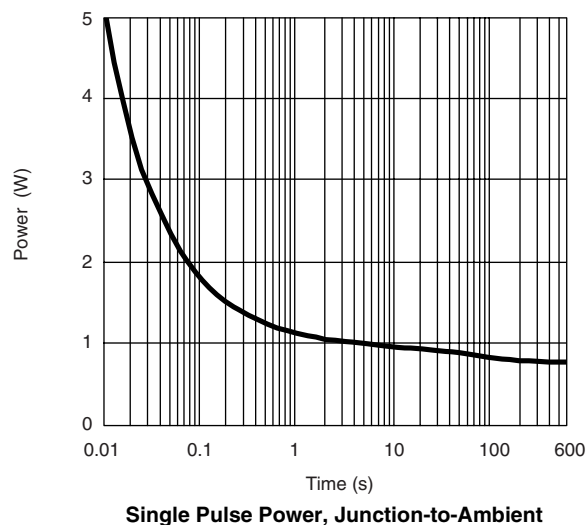
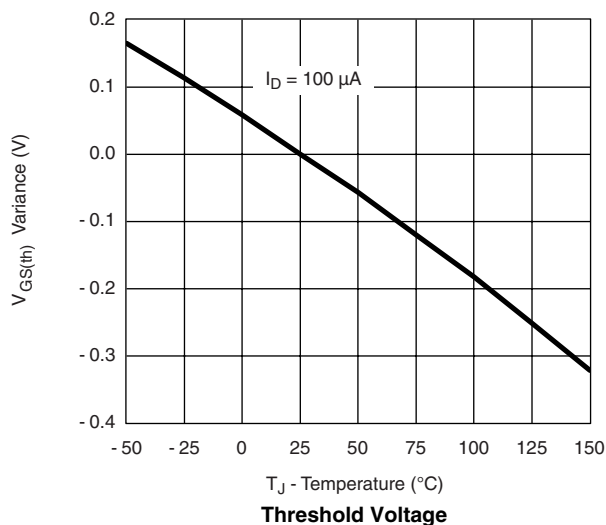
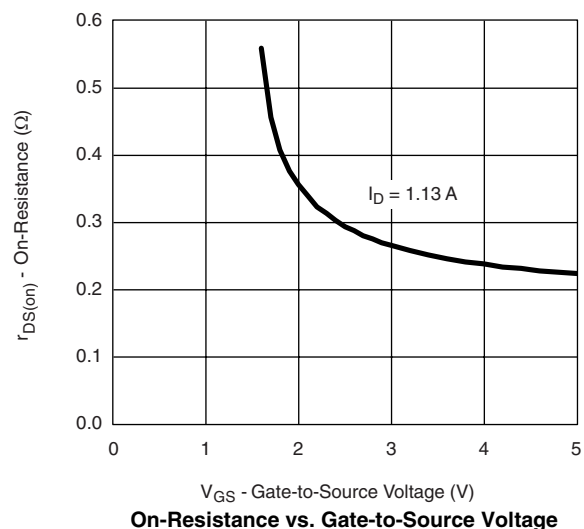
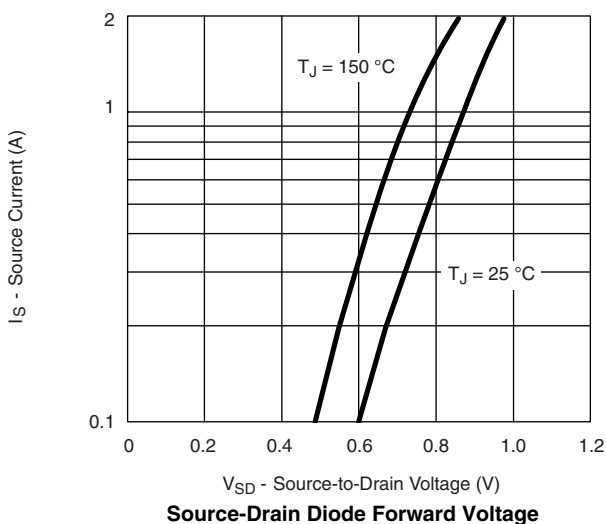
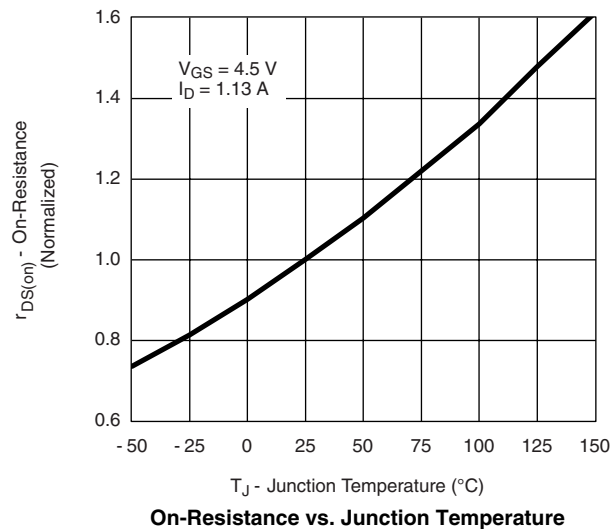
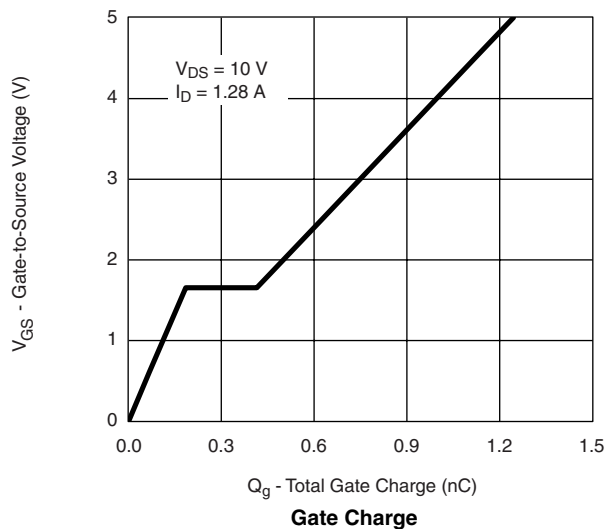
Notes:

a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

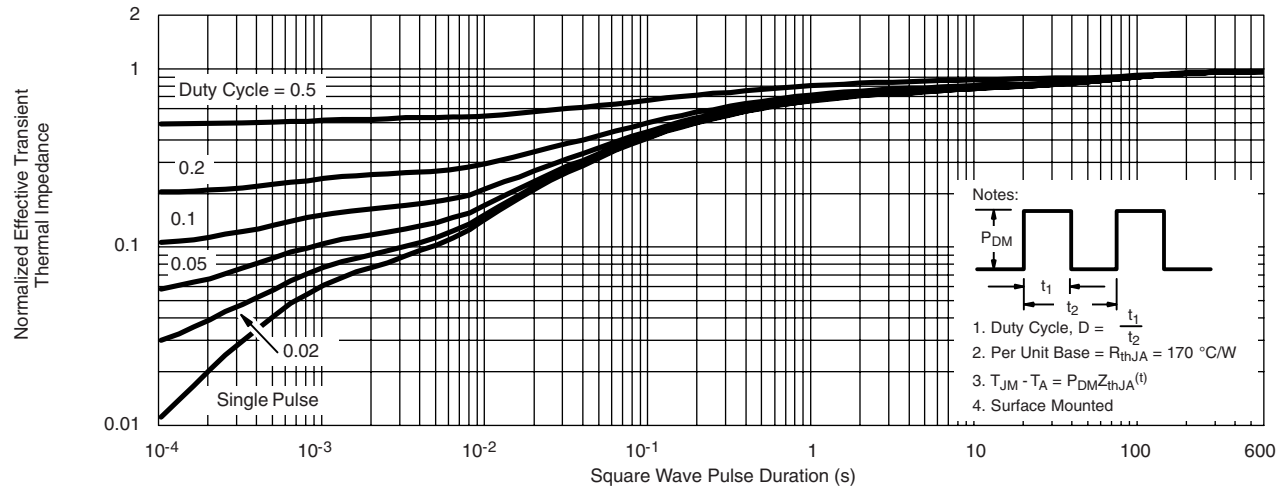
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Gate-Current vs. Gate-Source Voltage****Gate-Current vs. Gate-Source Voltage****Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance**

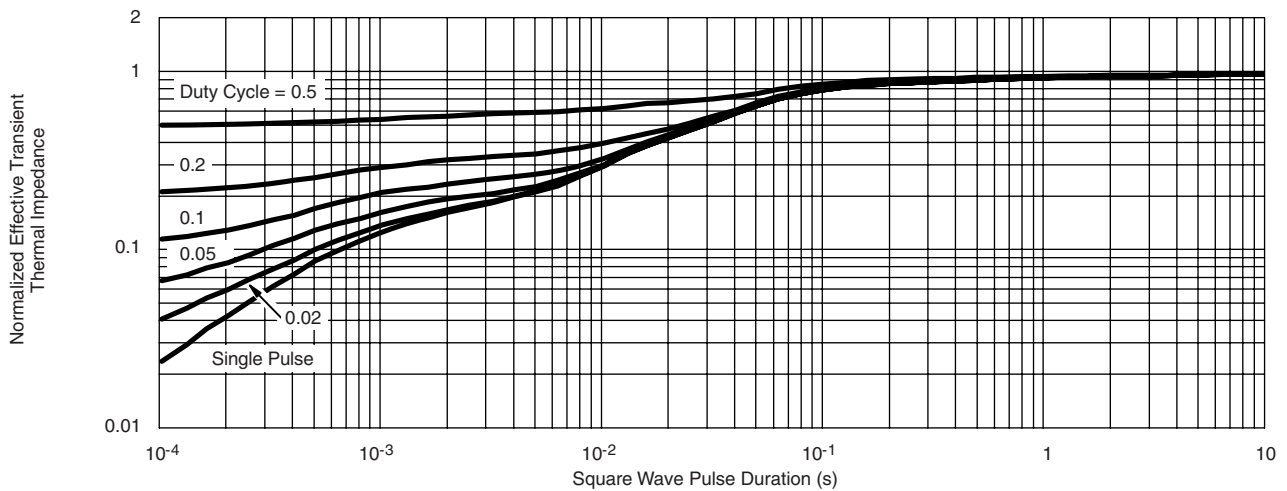
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



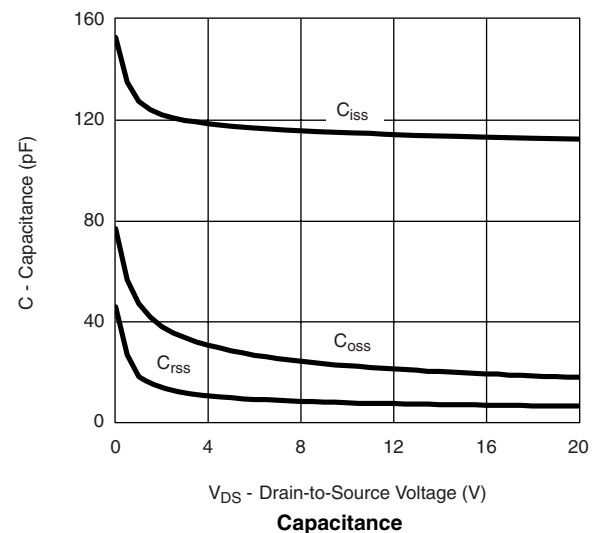
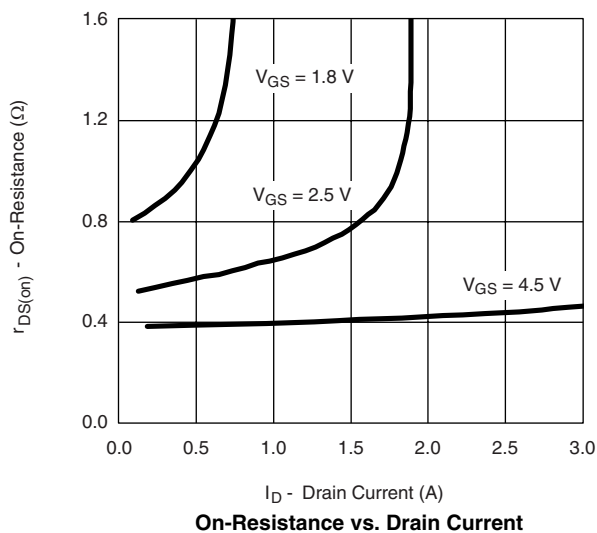
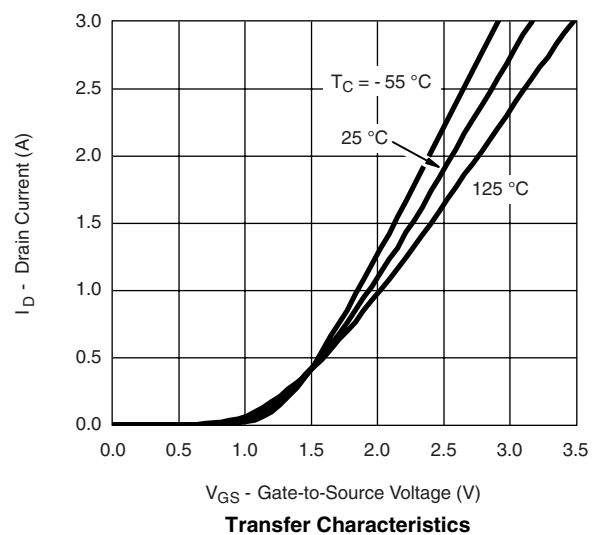
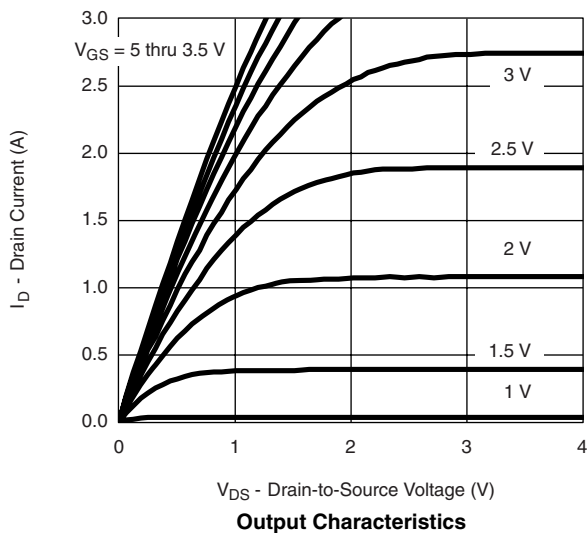
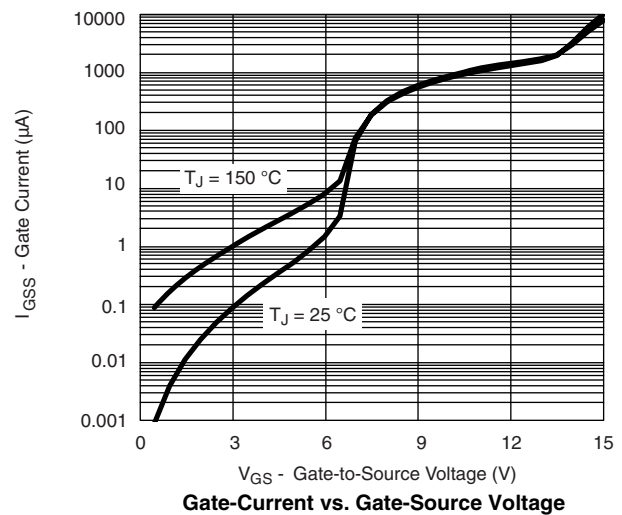
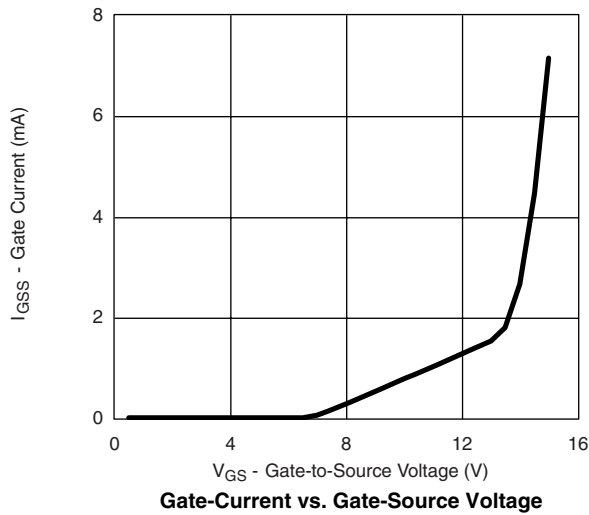
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

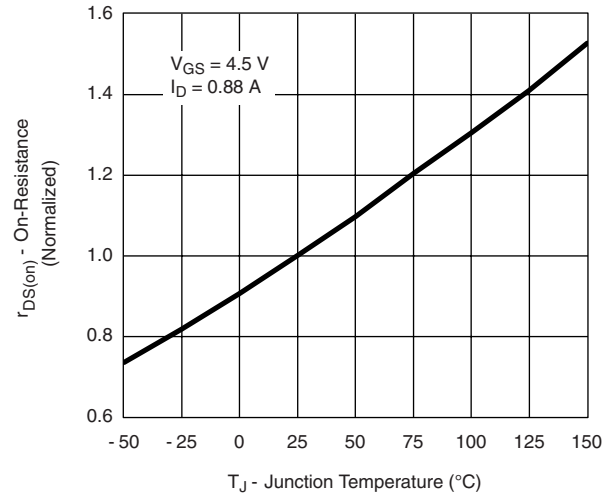
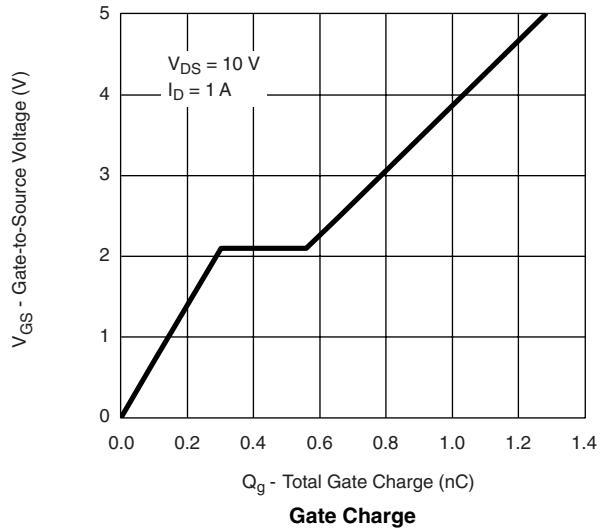
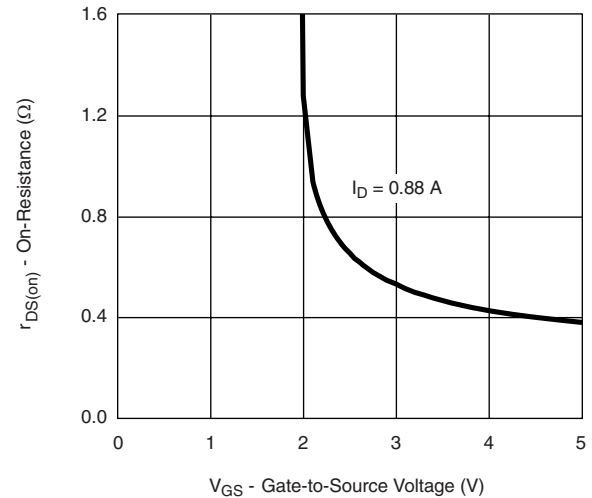
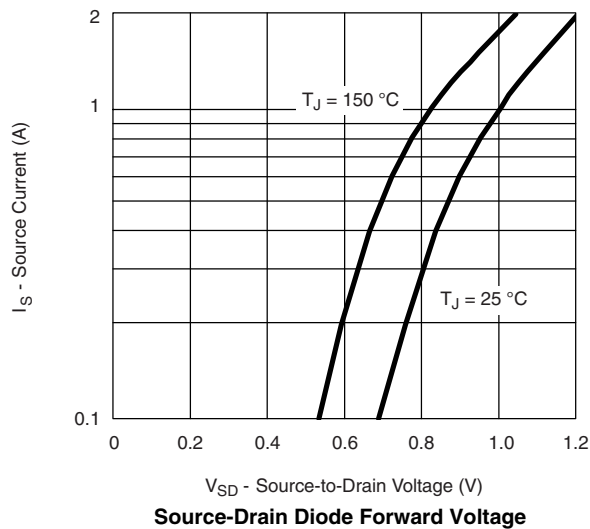
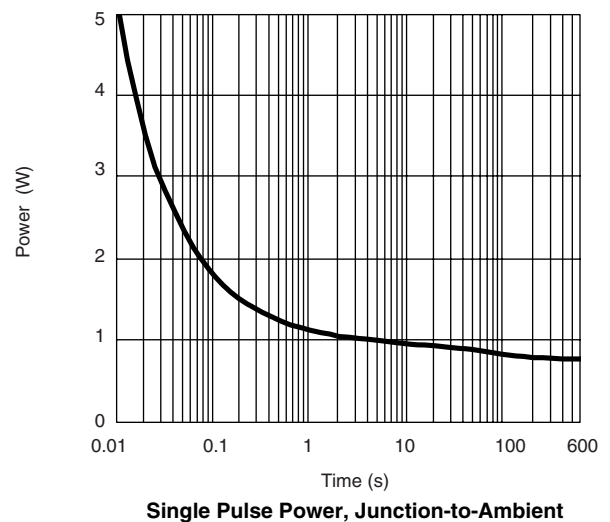
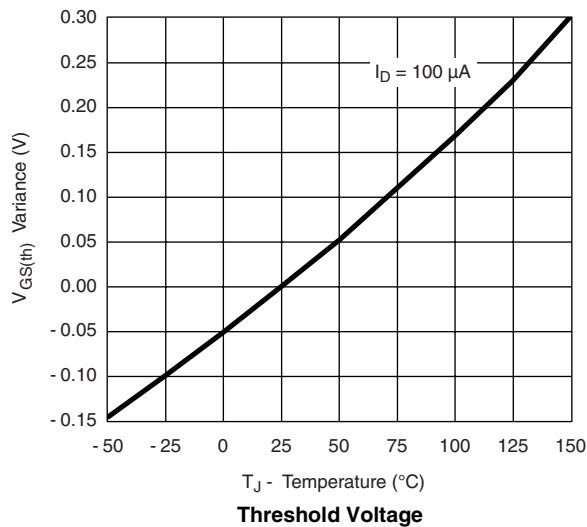


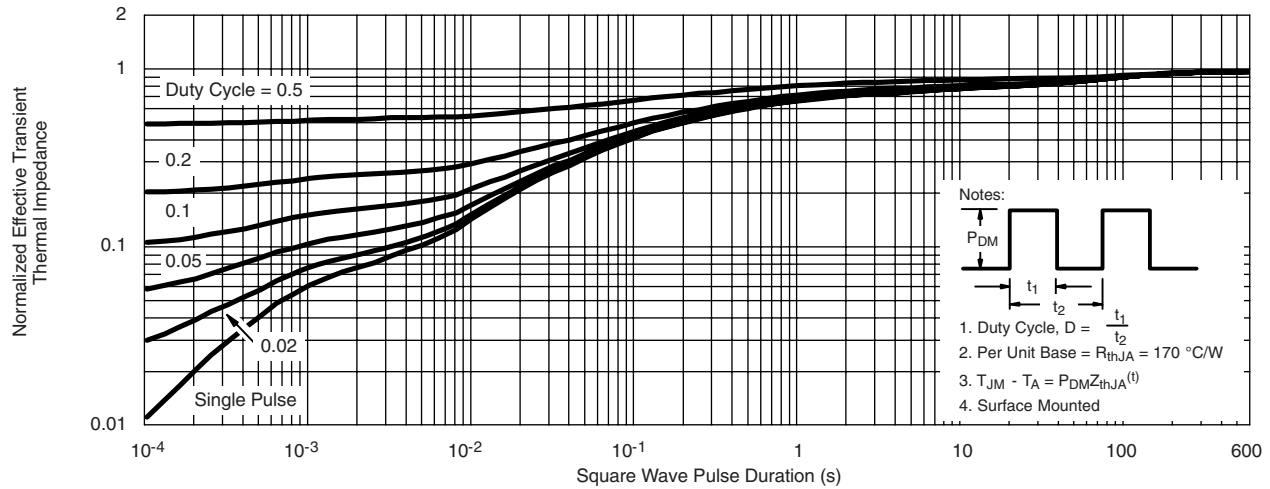
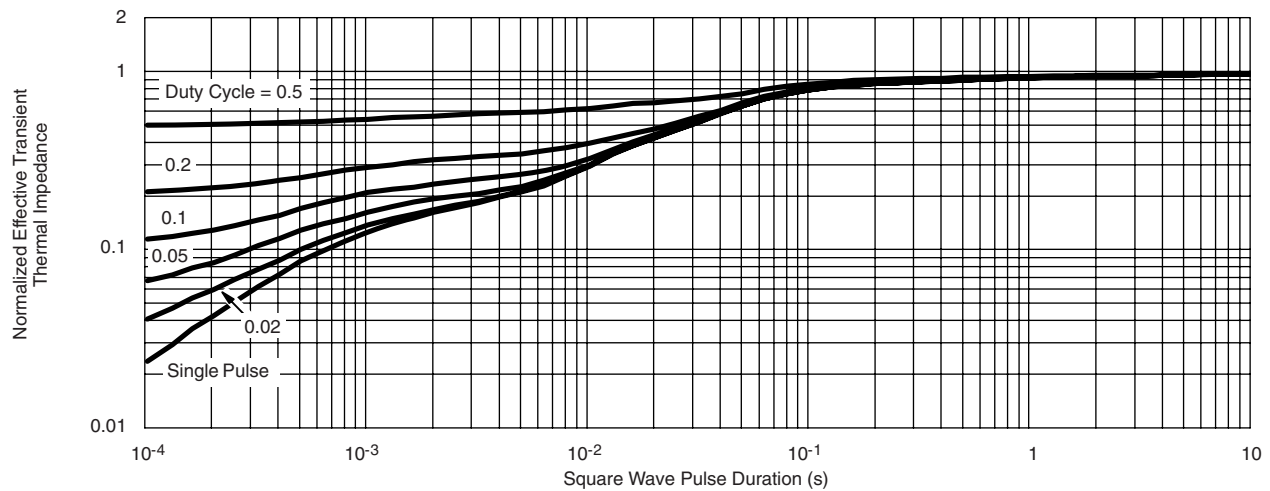
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****On-Resistance vs. Gate-to-Source Voltage**

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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